

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	2SK3019TL
Manufacturer:	Rohm Semiconductor
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/rohm-semiconductor/2sk3019tl.html>

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New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Small switching (30V, 0.1A)

2SK3019

●Applications

Interfacing, switching (30V, 100mA)

●Features

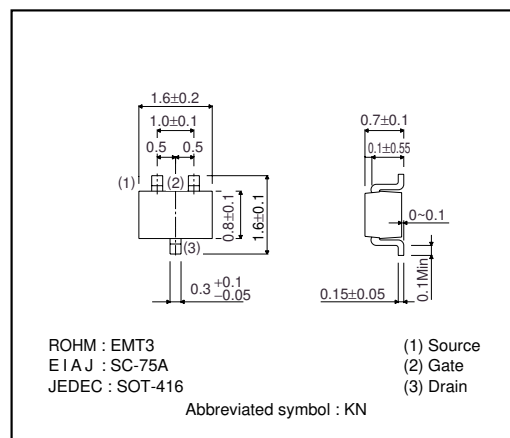
- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Low voltage drive (2.5V) makes this device ideal for portable equipment.
- 4) Easily designed drive circuits.
- 5) Easy to parallel.

●Structure

Silicon N-channel

MOSFET

●External dimensions (Units : mm)



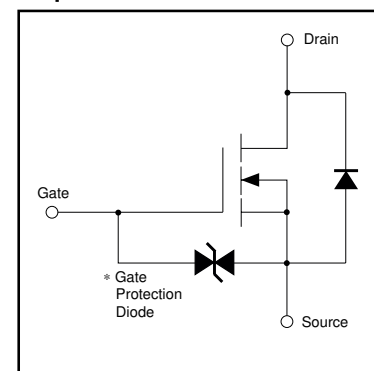
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	±20	V
Drain current	Continuous	I_D	100
	Pulsed	I_{DP}^{*1}	200
Reverse drain current	Continuous	I_{DR}	100
	Pulsed	I_{DRP}^{*1}	200
Total power dissipation (Tc=25°C)	P_D^{*2}	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55~+150	°C

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 50\%$

*2 With each pin mounted on the recommended lands.

●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use a protection circuit when the fixed voltages are exceeded.

Transistor

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{gss}	—	—	± 1	μA	$V_{GS}=\pm 20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D=10\mu A$, $V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	—	—	1.0	μA	$V_{DS}=30V$, $V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.8	—	1.5	V	$V_{DS}=3V$, $I_D=100\mu A$
Static drain-source on-state resistance	$R_{DS(on)}$	—	5	8	Ω	$I_D=10mA$, $V_{GS}=4V$
	$R_{DS(on)}$	—	7	13	Ω	$I_D=1mA$, $V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $	20	—	—	ms	$I_D=10mA$, $V_{DS}=3V$
Input capacitance	C_{iss}	—	13	—	pF	$V_{DS}=5V$
Output capacitance	C_{oss}	—	9	—	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	—	4	—	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D=10mA$, $V_{DD} \rightleftharpoons 5V$
Rise time	t_r	—	35	—	ns	$V_{GS}=5V$
Turn-off delay time	$t_{d(off)}$	—	80	—	ns	$R_L=500\Omega$
Fall time	t_f	—	80	—	ns	$R_{GS}=10\Omega$

●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SK3019		○

●Electrical characteristic curves

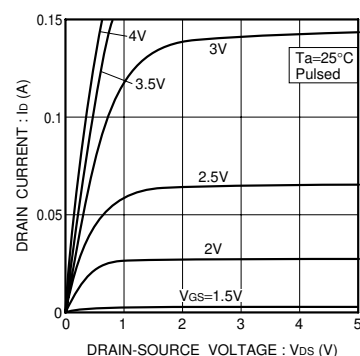


Fig.1 Typical output characteristics

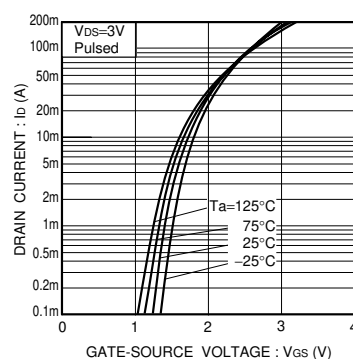


Fig.2 Typical transfer characteristics

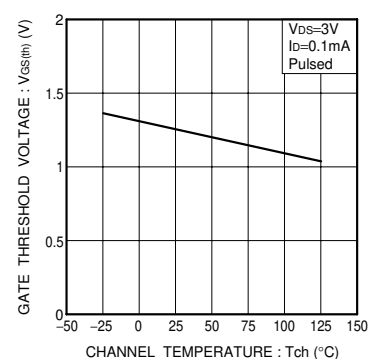


Fig.3 Gate threshold voltage vs. channel temperature

Transistor

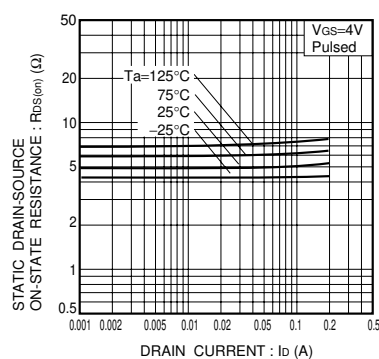


Fig.4 Static drain-source on-state resistance vs. drain current (I)

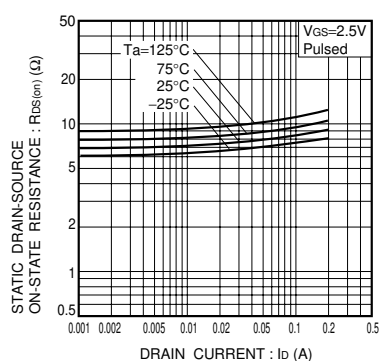


Fig.5 Static drain-source on-state resistance vs. drain current (II)

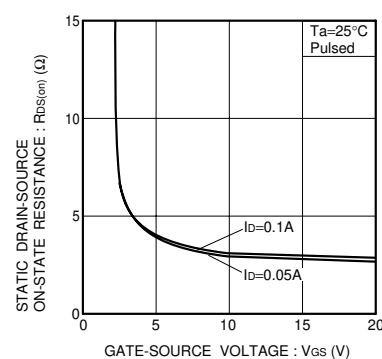


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

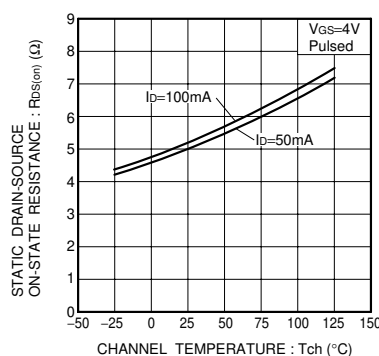


Fig.7 Static drain-source on-state resistance vs. channel temperature

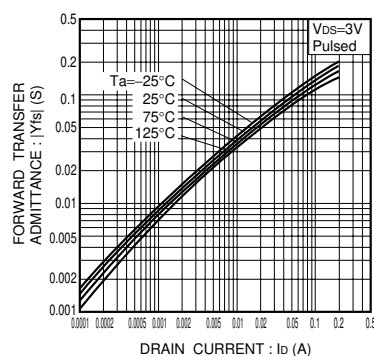


Fig.8 Forward transfer admittance vs. drain current

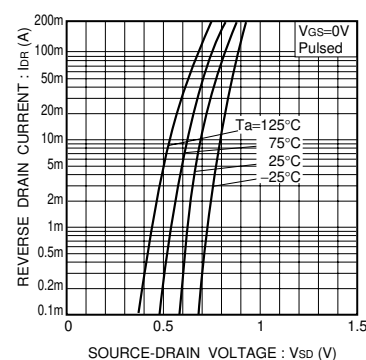


Fig.9 Reverse drain current vs. source-drain voltage (I)

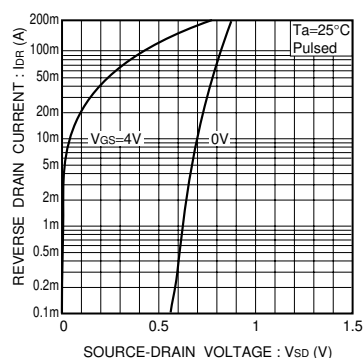


Fig.10 Reverse drain current vs. source-drain voltage (II)

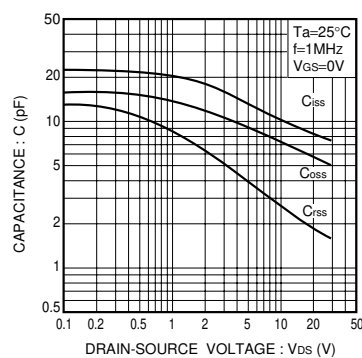


Fig.11 Typical capacitance vs. drain-source voltage

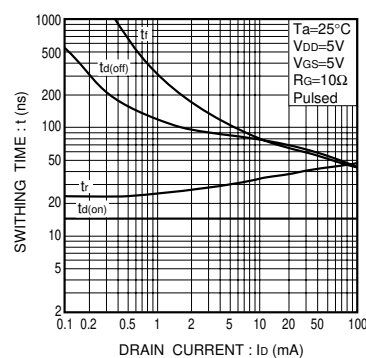


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

Transistor

● Switching characteristics measurement circuit

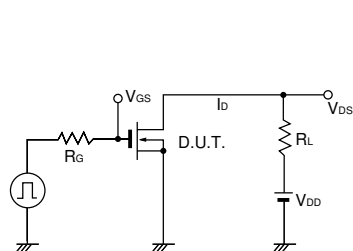


Fig.13 Switching time measurement circuit

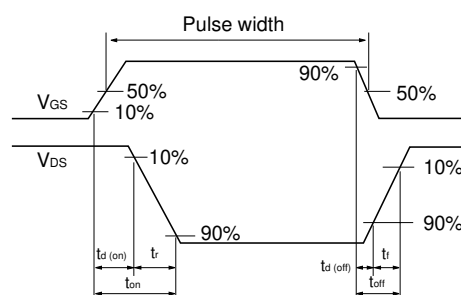


Fig.14 Switching time waveforms